

$V_{DSS}$	600V
$R_{DS(on)}(Max.)$	0.3 $\Omega$
$I_D$	$\pm 15A$
$P_D$	110W

●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage ( $V_{GSS}$ ) guaranteed to be  $\pm 30V$ .
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating ; RoHS compliant

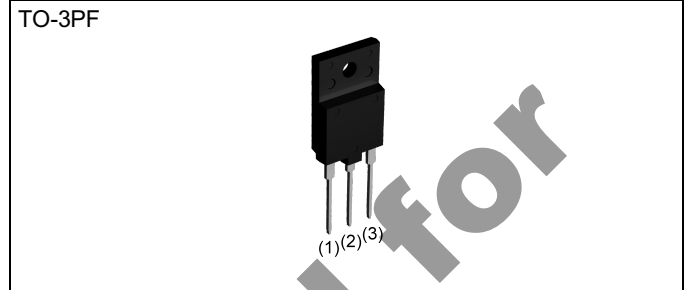
●Application

Switching Power Supply

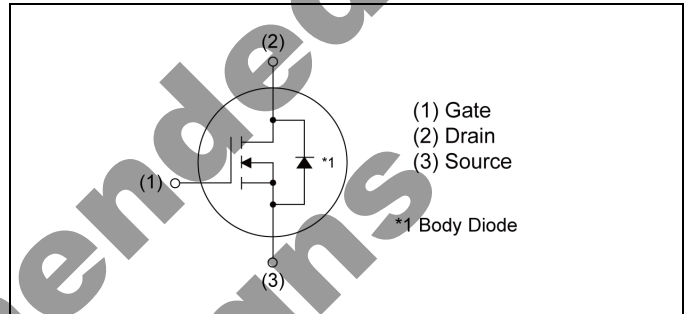
●Absolute maximum ratings ( $T_a = 25^\circ C$ )

Parameter	Symbol	Value	Unit	
Drain - Source voltage	$V_{DSS}$	600	V	
Continuous drain current	$T_C = 25^\circ C$	$I_D^{*1}$	$\pm 15$	A
	$T_C = 100^\circ C$	$I_D^{*1}$	$\pm 7.1$	A
Pulsed drain current	$I_{D,pulse}^{*2}$	$\pm 60$	A	
Gate - Source voltage	$V_{GSS}$	$\pm 30$	V	
Avalanche energy, single pulse	$E_{AS}^{*3}$	15	mJ	
Avalanche energy, repetitive	$E_{AR}^{*4}$	9.1	mJ	
Avalanche current	$I_{AR}^{*3}$	7.5	A	
Power dissipation ( $T_c = 25^\circ C$ )	$P_D$	110	W	
Junction temperature	$T_j$	150	$^\circ C$	
Range of storage temperature	$T_{stg}$	-55 to +150	$^\circ C$	
Reverse diode dv/dt	dv/dt	15	V/ns	

●Outline



●Inner circuit



●Packaging specifications

Type	Packing	Tube
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	360
	Taping code	C8
	Marking	R6015ANZ

### ● Absolute maximum ratings

Parameter	Symbol	Conditions	Values	Unit
Drain - Source voltage slope	dv/dt	$V_{DS} = 480V, I_D = 15A$ $T_j = 125^\circ C$	50	V/ns

### ● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.13	$^\circ C/W$
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	40	$^\circ C/W$
Soldering temperature, wavesoldering for 10s	$T_{sold}$	-	-	265	$^\circ C$

### ● Electrical characteristics ( $T_a = 25^\circ C$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	600	-	-	V
Drain - Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS} = 0V, I_D = 7.5A$	-	700	-	V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 600V, V_{GS} = 0V$ $T_j = 25^\circ C$	-	0.1	100	$\mu A$
		$T_j = 125^\circ C$	-	-	1000	
Gate - Source leakage current	$I_{GSS}$	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	$\pm 100$	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	2.95	-	4.15	V
Static drain - source on - state resistance	$R_{DS(on)}^{*6}$	$V_{GS} = 10V, I_D = 7.5A$ $T_j = 25^\circ C$	-	0.23	0.3	$\Omega$
		$T_j = 125^\circ C$	-	0.46	-	
Gate input resistance	$R_G$	f = 1MHz, open drain	-	10.1	-	$\Omega$

**●Electrical characteristics** ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Transconductance	$g_{fs}^{*6}$	$V_{DS} = 10\text{V}, I_D = 7.5\text{A}$	4.5	12	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{V}$	-	1700	-	pF
Output capacitance	$C_{oss}$	$V_{DS} = 25\text{V}$	-	1120	-	
Reverse transfer capacitance	$C_{rss}$	$f = 1\text{MHz}$	-	80	-	
Effective output capacitance, energy related	$C_{o(er)}$	$V_{GS} = 0\text{V},$ $V_{DS} = 0\text{V to } 480\text{V}$	-	64.7	-	pF
Effective output capacitance, time related	$C_{o(tr)}$		-	204	-	
Turn - on delay time	$t_{d(on)}^{*6}$	$V_{DD} \approx 300\text{V}, V_{GS} = 10\text{V}$	-	50	-	ns
Rise time	$t_r^{*6}$	$I_D = 7.5\text{A}$	-	50	-	
Turn - off delay time	$t_{d(off)}^{*6}$	$R_L = 40\Omega$	-	150	300	
Fall time	$t_f^{*6}$	$R_G = 10\Omega$	-	60	120	

**●Gate charge characteristics** ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	$Q_g^{*6}$	$V_{DD} \approx 300\text{V}$	-	50	-	nC
Gate - Source charge	$Q_{gs}^{*6}$	$I_D = 15\text{A}$	-	8	-	
Gate - Drain charge	$Q_{gd}^{*6}$	$V_{GS} = 10\text{V}$	-	20	-	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} \approx 300\text{V}, I_D = 15\text{A}$	-	5.6	-	V

\*1 Limited only by maximum temperature allowed.

\*2  $P_w \leq 10\mu\text{s}$ , Duty cycle  $\leq 1\%$

\*3  $L \approx 500\mu\text{H}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\Omega$ , starting  $T_j = 25^\circ\text{C}$

\*4  $L \approx 500\mu\text{H}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\Omega$ , starting  $T_j = 25^\circ\text{C}$ ,  $f = 10\text{kHz}$

\*5 Reference measurement circuits Fig.5-1.

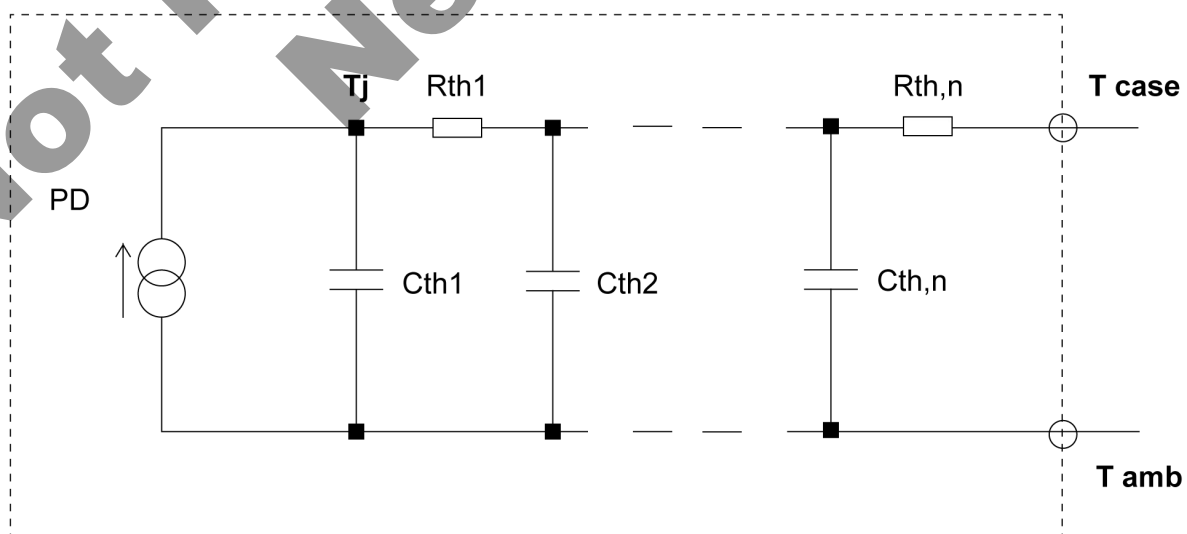
\*6 Pulsed

●Body diode electrical characteristics (Source-Drain) ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	$I_S^{*1}$	$T_C = 25^\circ\text{C}$	-	-	15	A
Inverse diode direct current, pulsed	$I_{SM}^{*2}$		-	-	60	A
Forward voltage	$V_{SD}^{*6}$	$V_{GS} = 0\text{V}, I_S = 15\text{A}$	-	-	1.5	V
Reverse recovery time	$t_{rr}^{*6}$	$I_S = 15\text{A}$ $di/dt = 100\text{A}/\mu\text{s}$	-	409	-	ns
Reverse recovery charge	$Q_{rr}^{*6}$		-	6.3	-	$\mu\text{C}$
Peak reverse recovery current	$I_{rm}^{*6}$		-	26	-	A
Peak rate of fall of reverse recovery current	$di_{rr}/dt$	$T_j = 25^\circ\text{C}$	-	700	-	$\text{A}/\mu\text{s}$

●Typical transient thermal characteristics

Symbol	Value	Unit	Symbol	Value	Unit
$R_{th1}$	0.106	K/W	$C_{th1}$	0.00538	Ws/K
$R_{th2}$	0.516		$C_{th2}$	0.0467	
$R_{th3}$	1.15		$C_{th3}$	1.09	



● Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

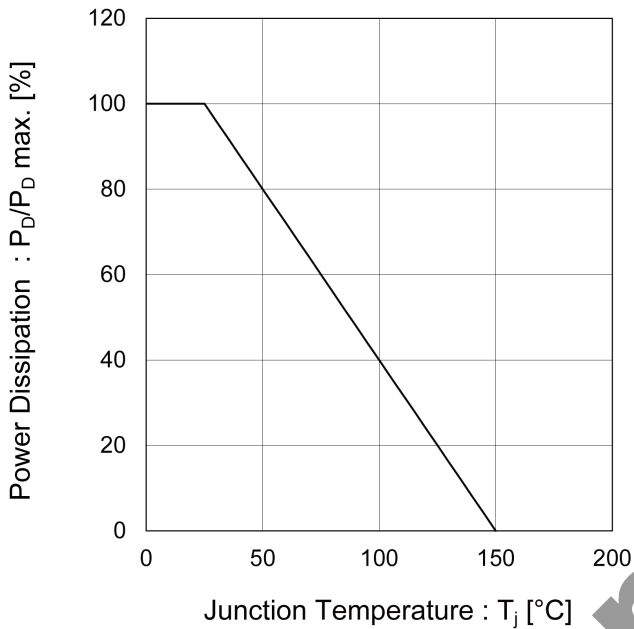


Fig.2 Maximum Safe Operating Area

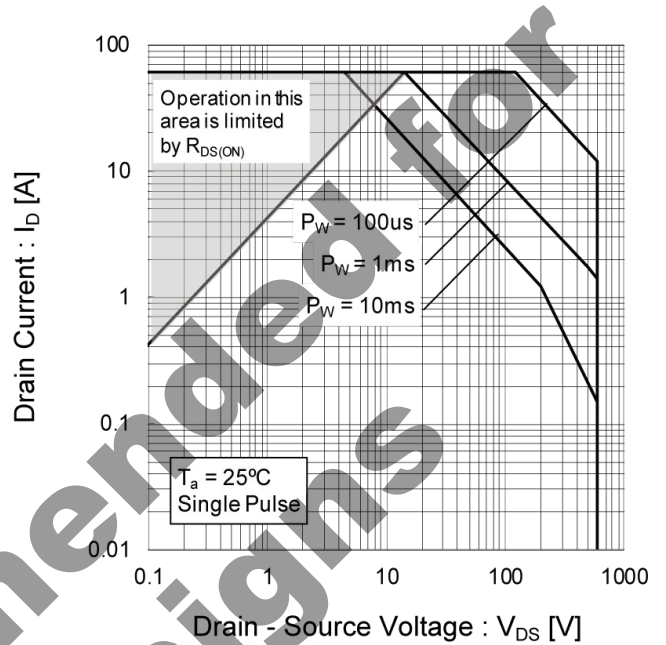
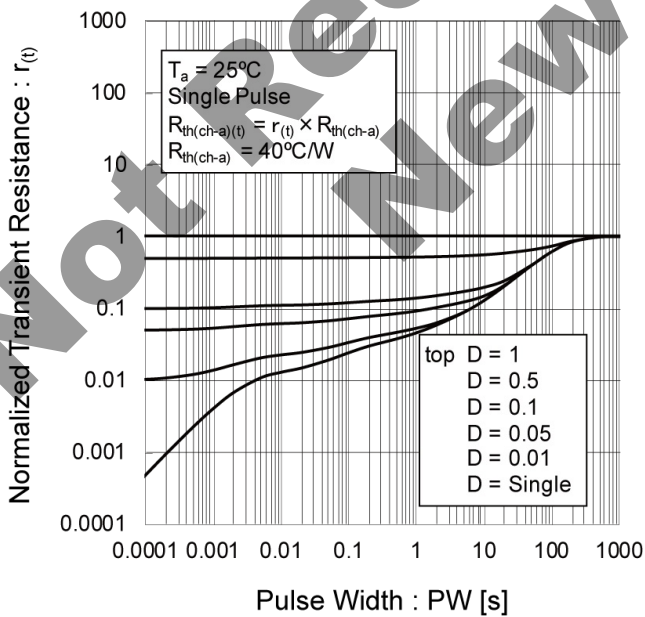


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



● Electrical characteristic curves

Fig.4 Avalanche Current vs. Inductive Load

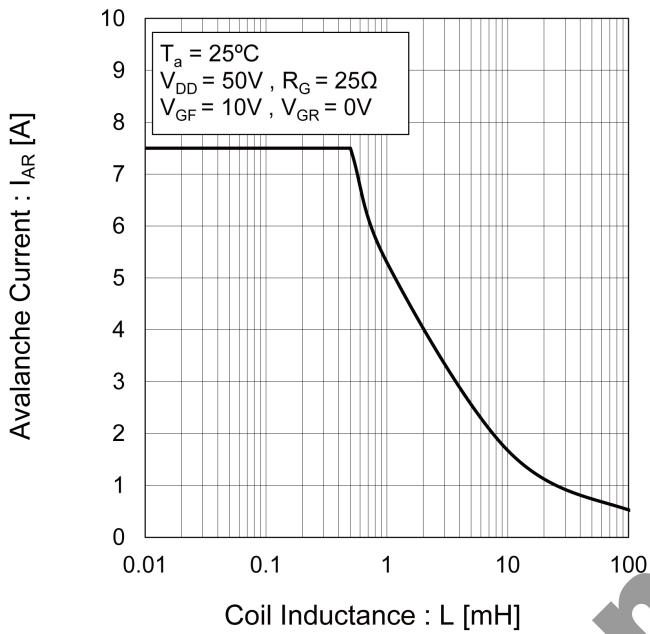


Fig.5 Avalanche Power Losses

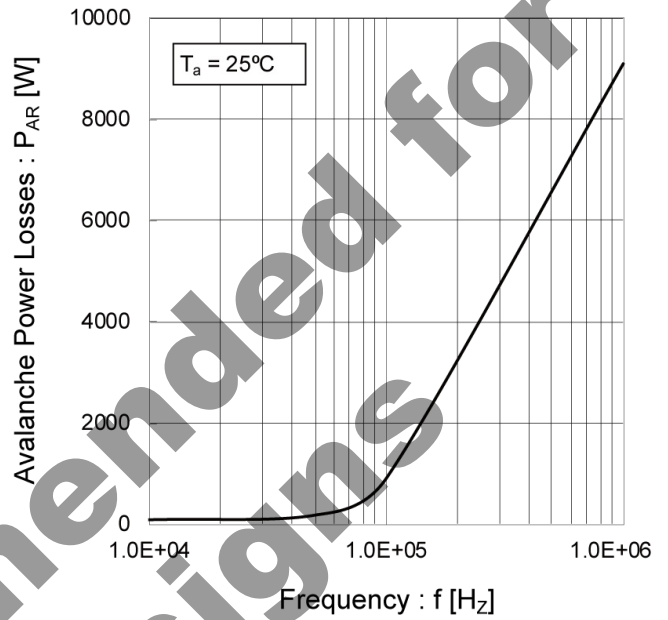
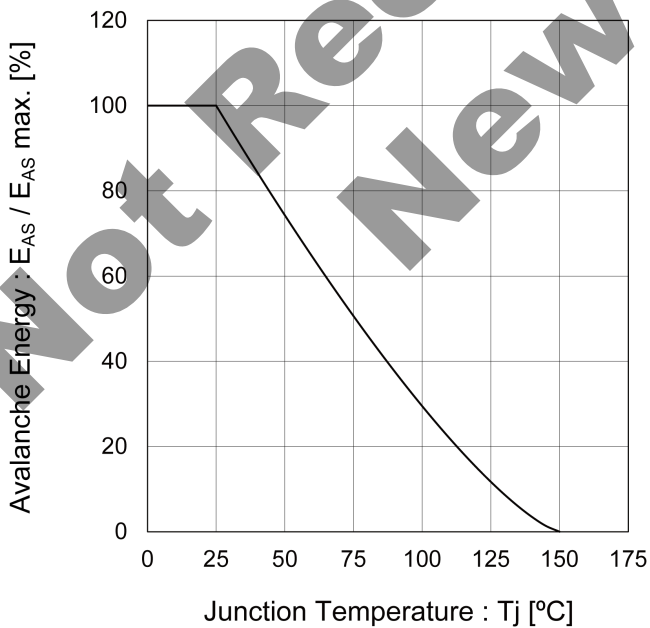


Fig.6 Avalanche Energy Derating Curve vs. Junction Temperature



● Electrical characteristic curves

Fig.7 Typical Output Characteristics(I)

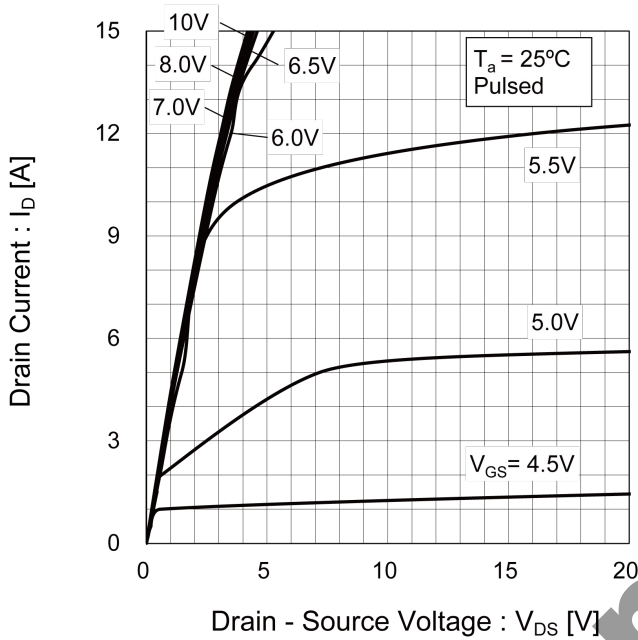


Fig.8 Typical Output Characteristics(II)

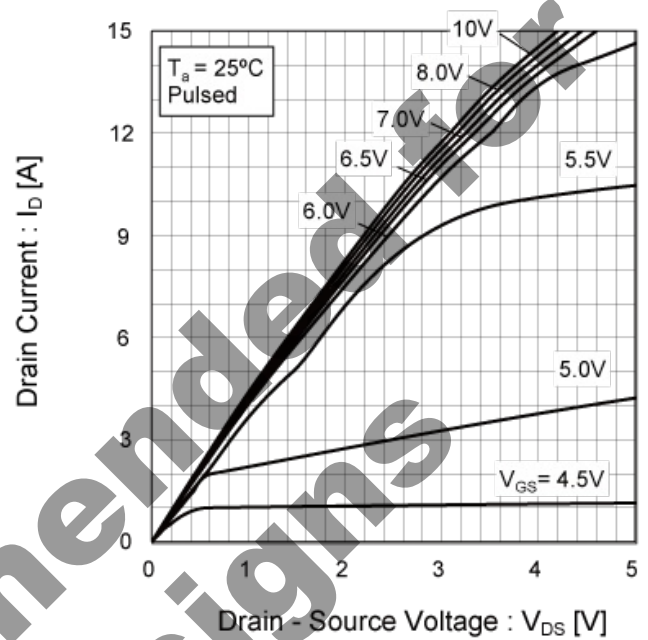


Fig.9  $T_j = 150^\circ\text{C}$  Typical Output Characteristics (I)

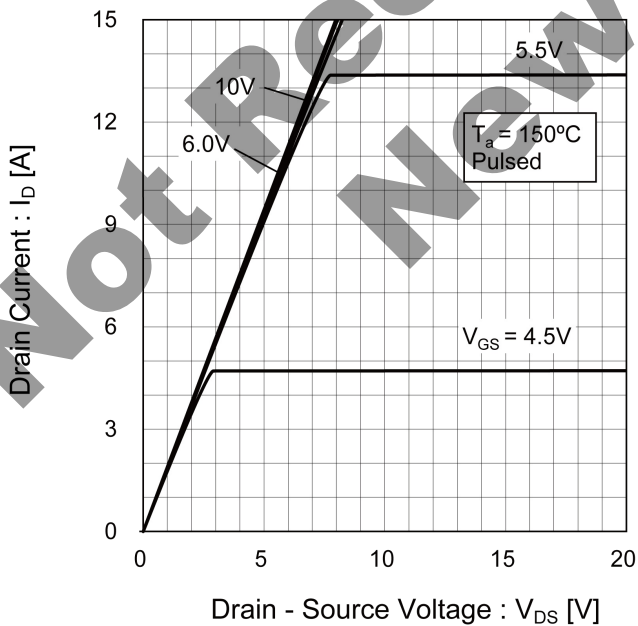
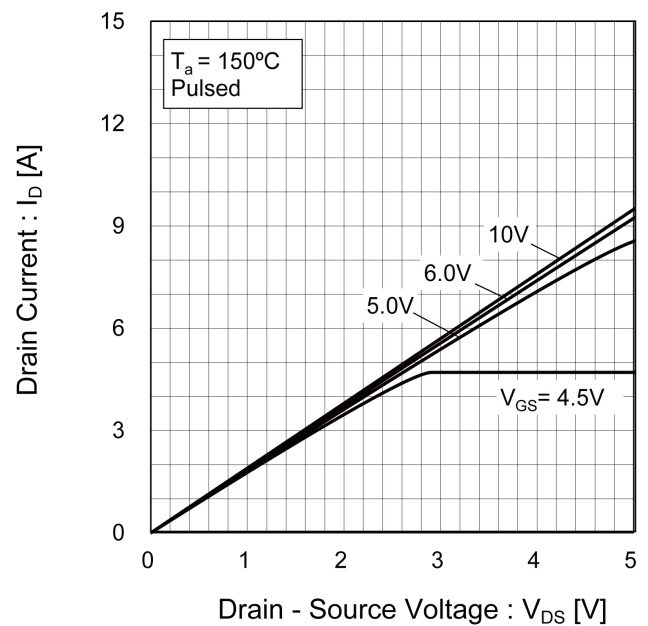


Fig.10  $T_j = 150^\circ\text{C}$  Typical Output Characteristics (II)



● Electrical characteristic curves

Fig.11 Breakdown Voltage vs. Junction Temperature

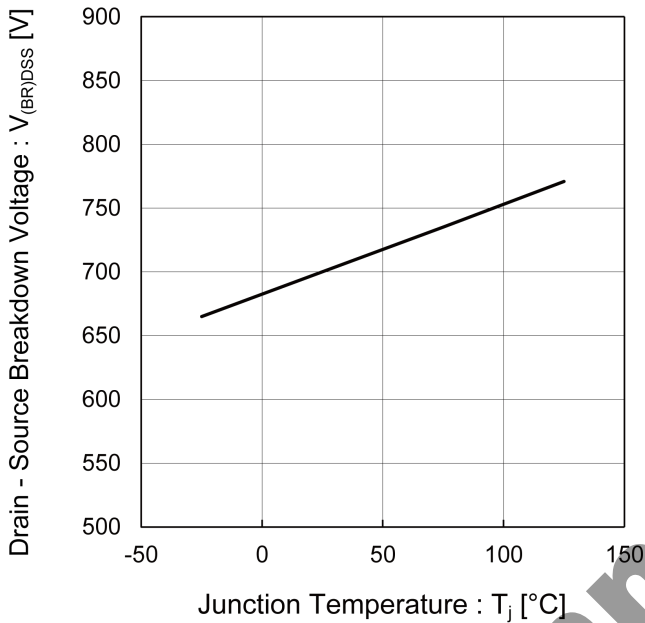


Fig.12 Typical Transfer Characteristics

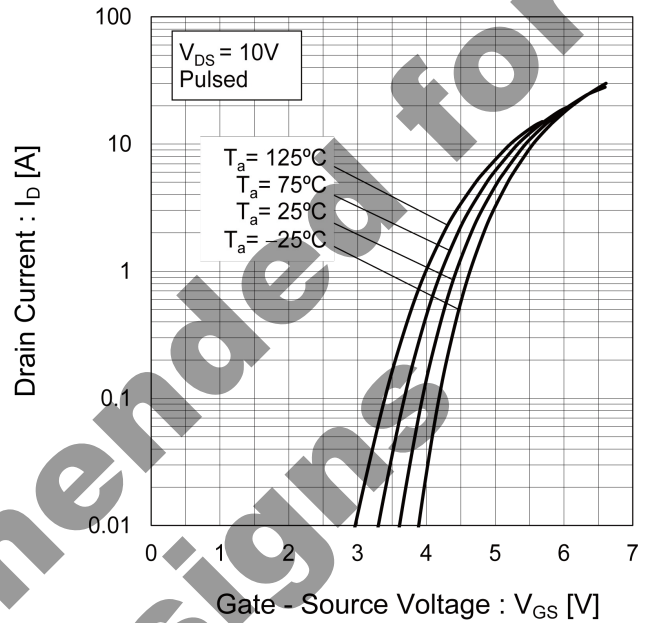


Fig.13 Gate Threshold Voltage vs. Junction Temperature

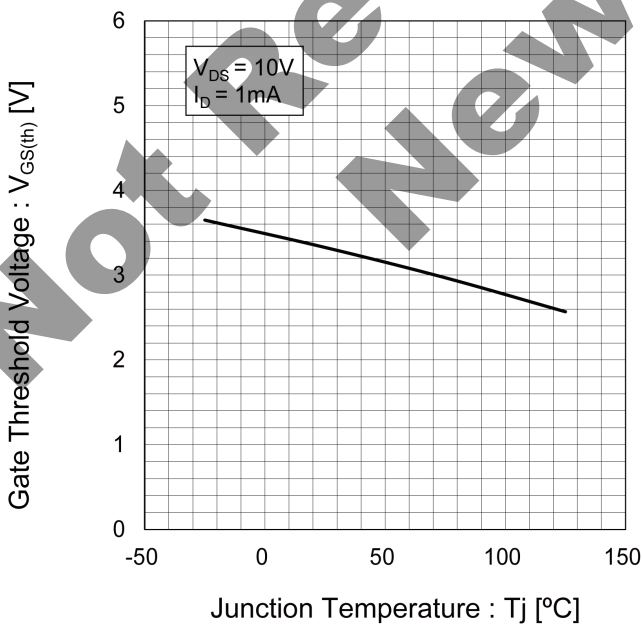
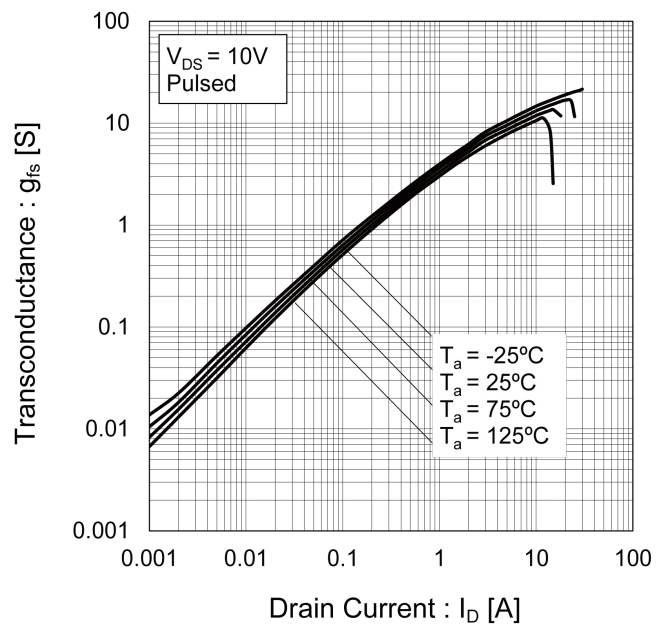


Fig.14 Transconductance vs. Drain Current





● Electrical characteristic curves

Fig.15 Static Drain - Source On - State Resistance vs. Gate Source Voltage

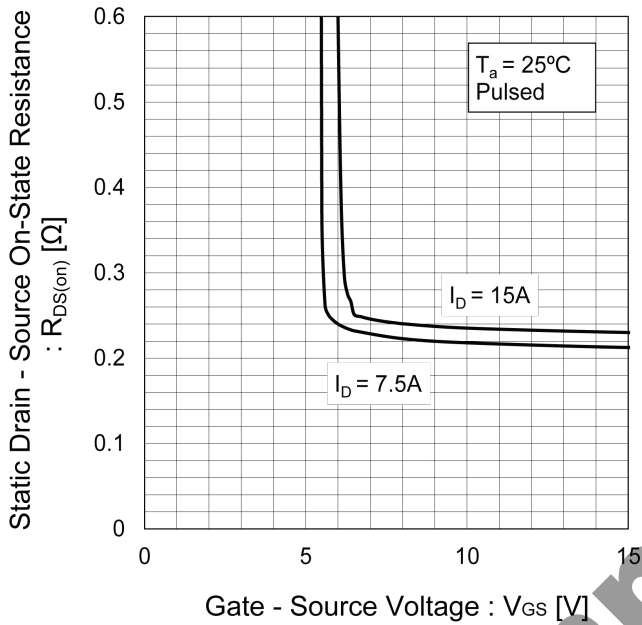


Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature

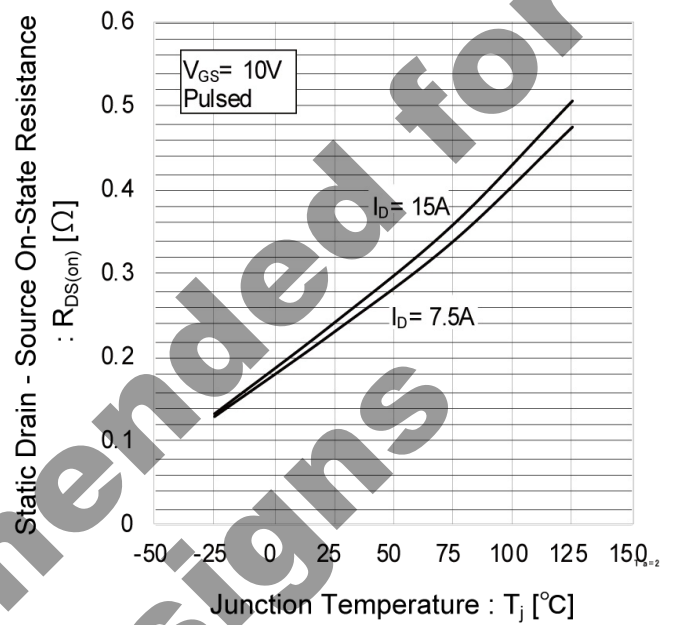
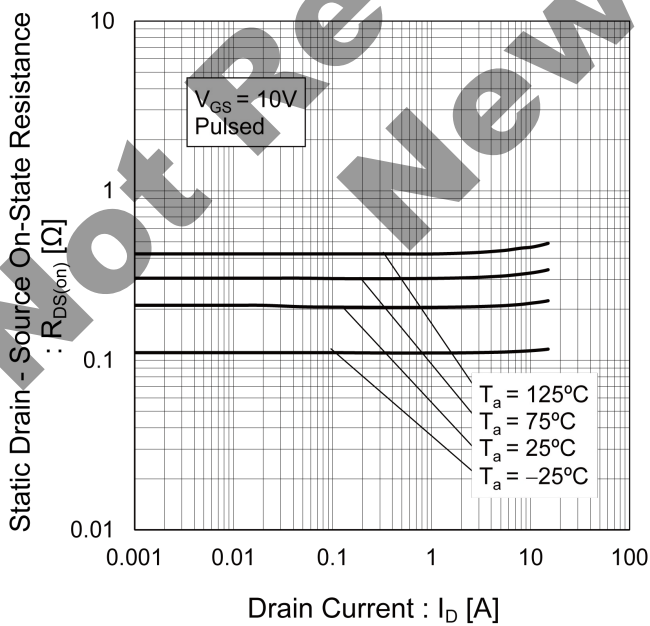


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current



● Electrical characteristic curves

Fig.18 Typical Capacitance vs. Drain - Source Voltage

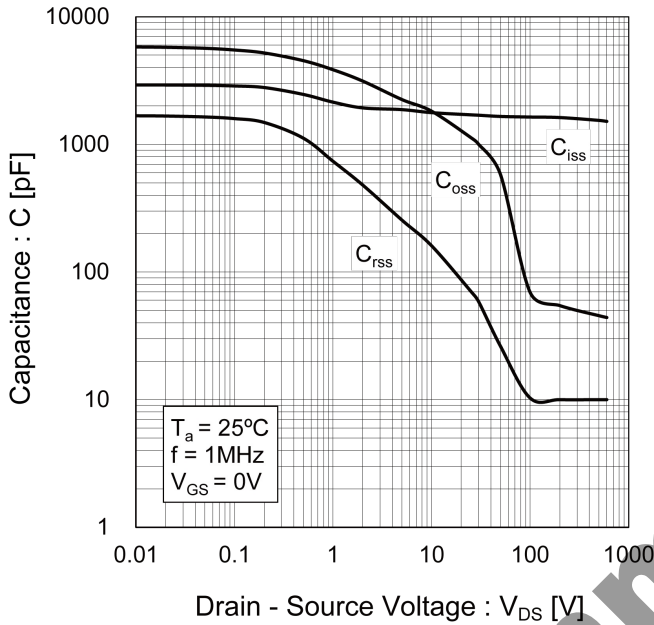


Fig.19 Coss Stored Energy

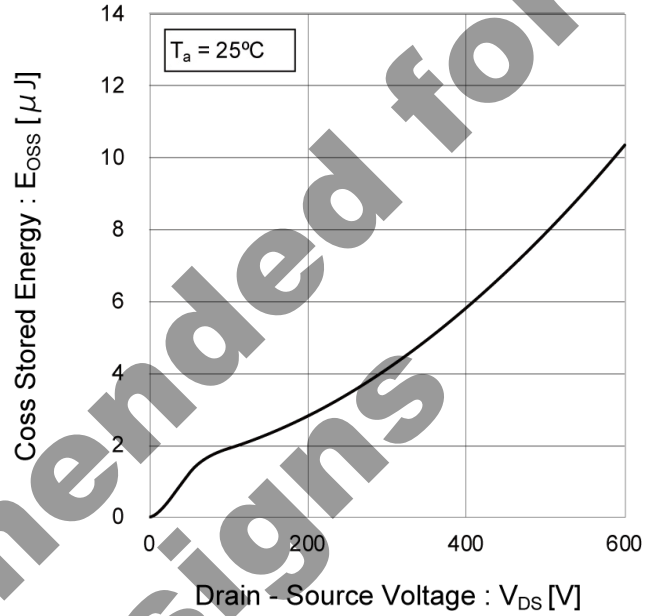


Fig.20 Switching Characteristics

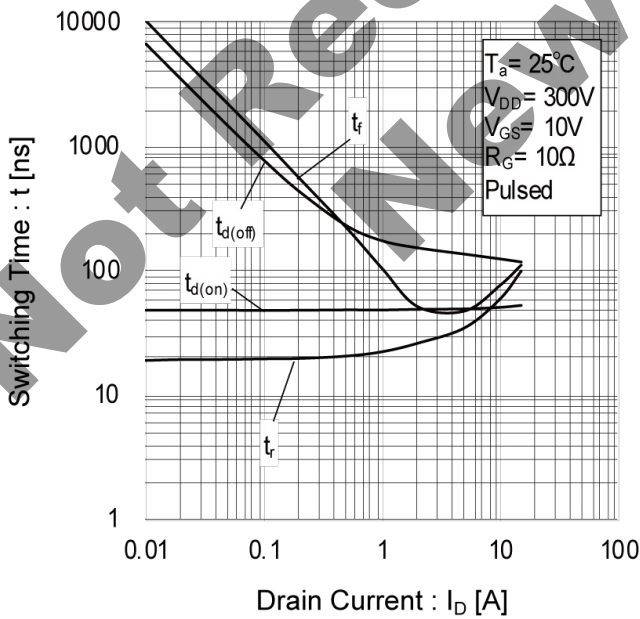
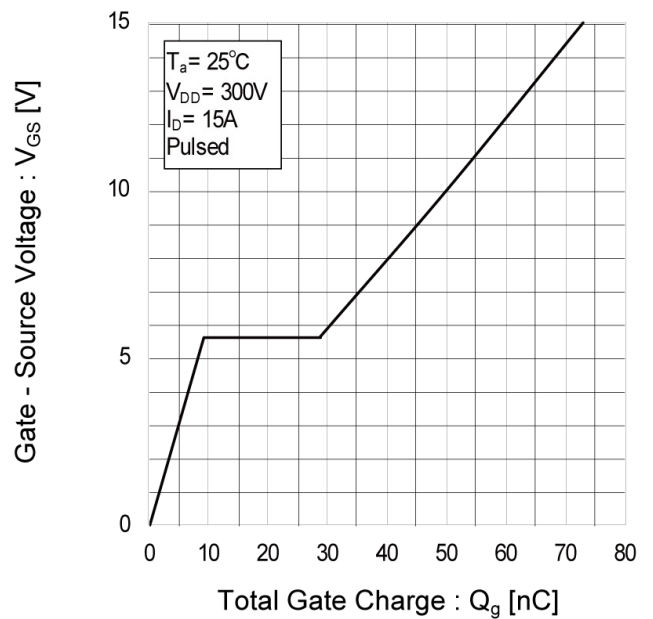


Fig.21 Dynamic Input Characteristics



● Electrical characteristic curves

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage

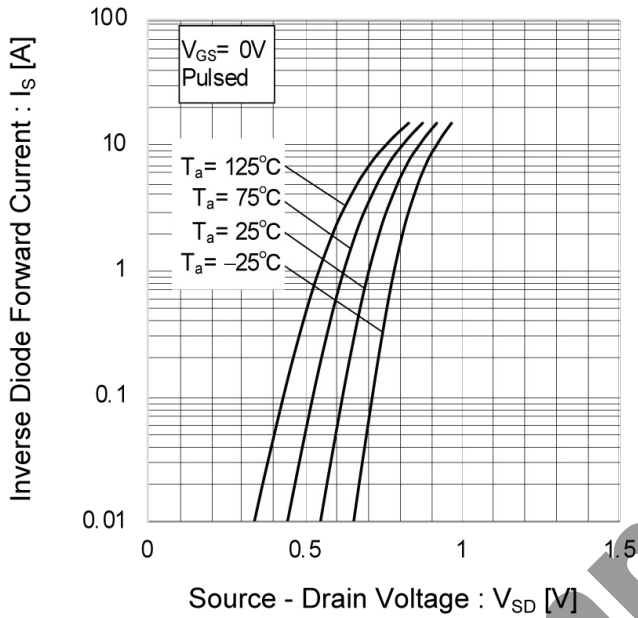
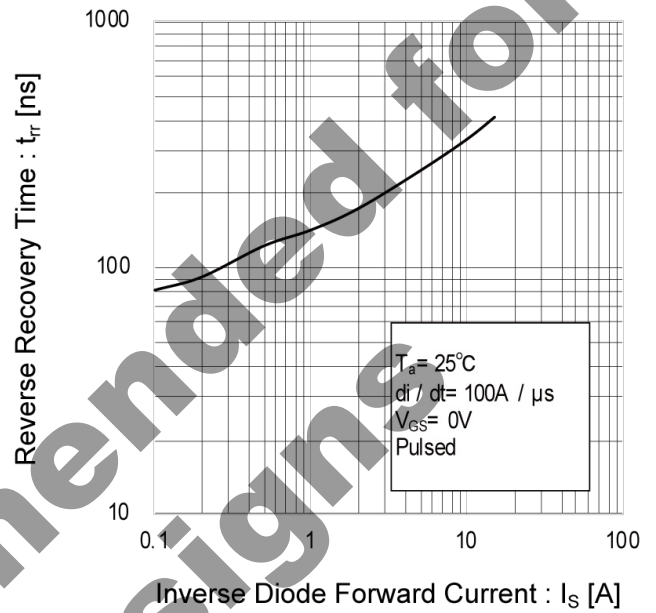


Fig.23 Reverse Recovery Time vs. Inverse Diode Forward Current



Not Recommended for New Design

● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

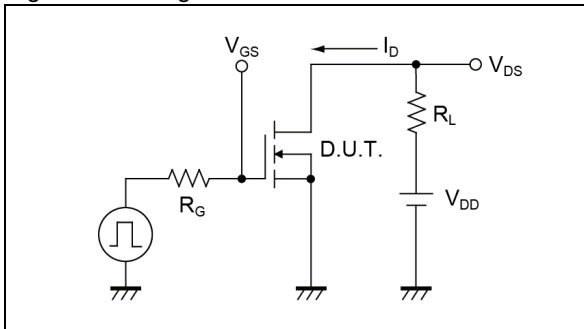


Fig.1-2 Switching Waveforms

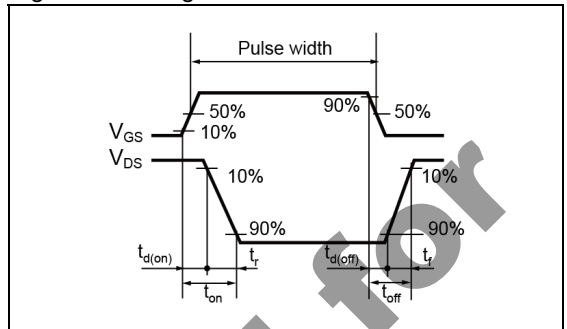


Fig.2-1 Gate Charge Measurement Circuit

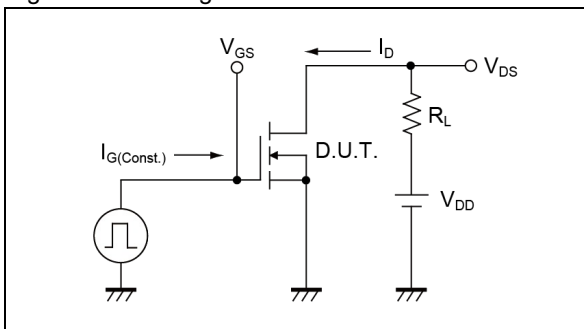


Fig.2-2 Gate Charge Waveform

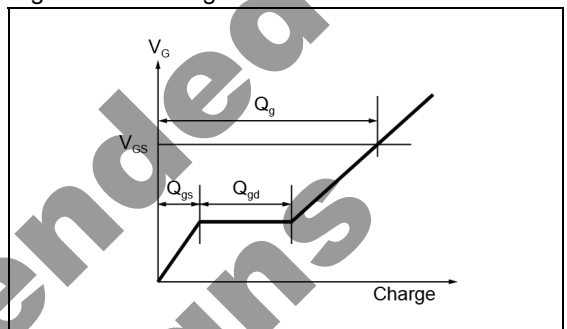


Fig.3-1 Avalanche Measurement Circuit

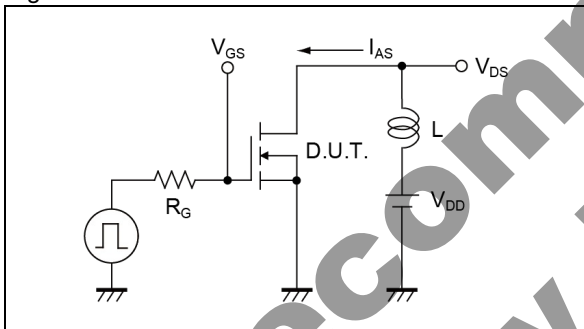


Fig.3-2 Avalanche Waveform

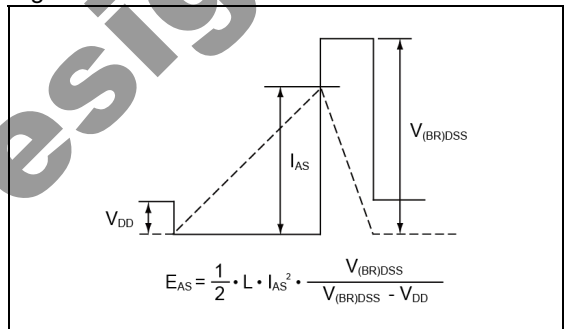


Fig.4-1 dv/dt Measurement Circuit

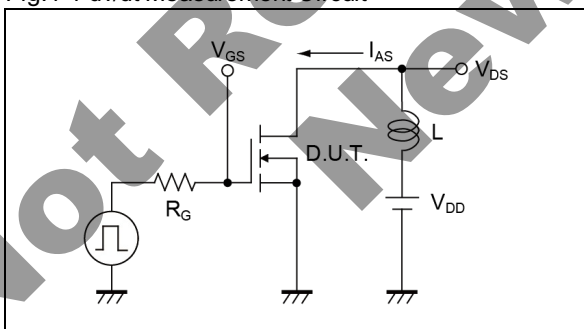


Fig.4-2 dv/dt Waveform

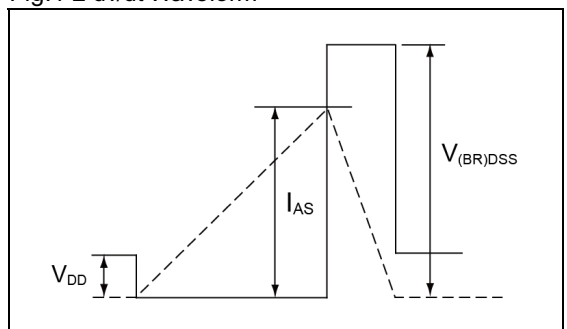


Fig.5-1 di/dt Measurement Circuit

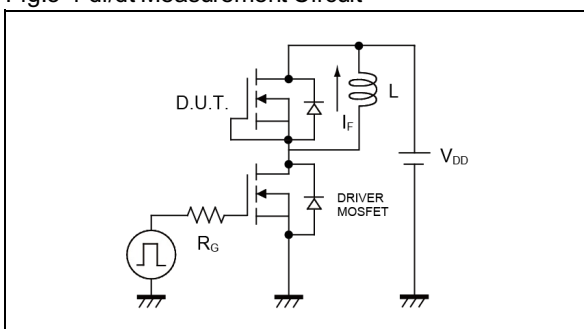
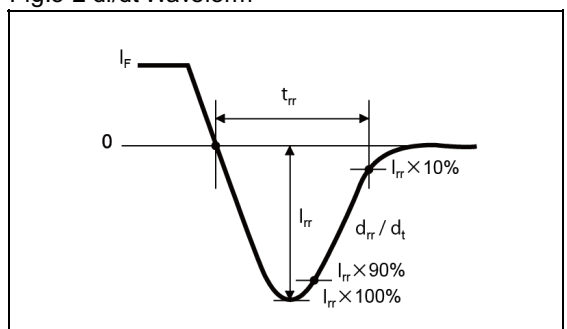
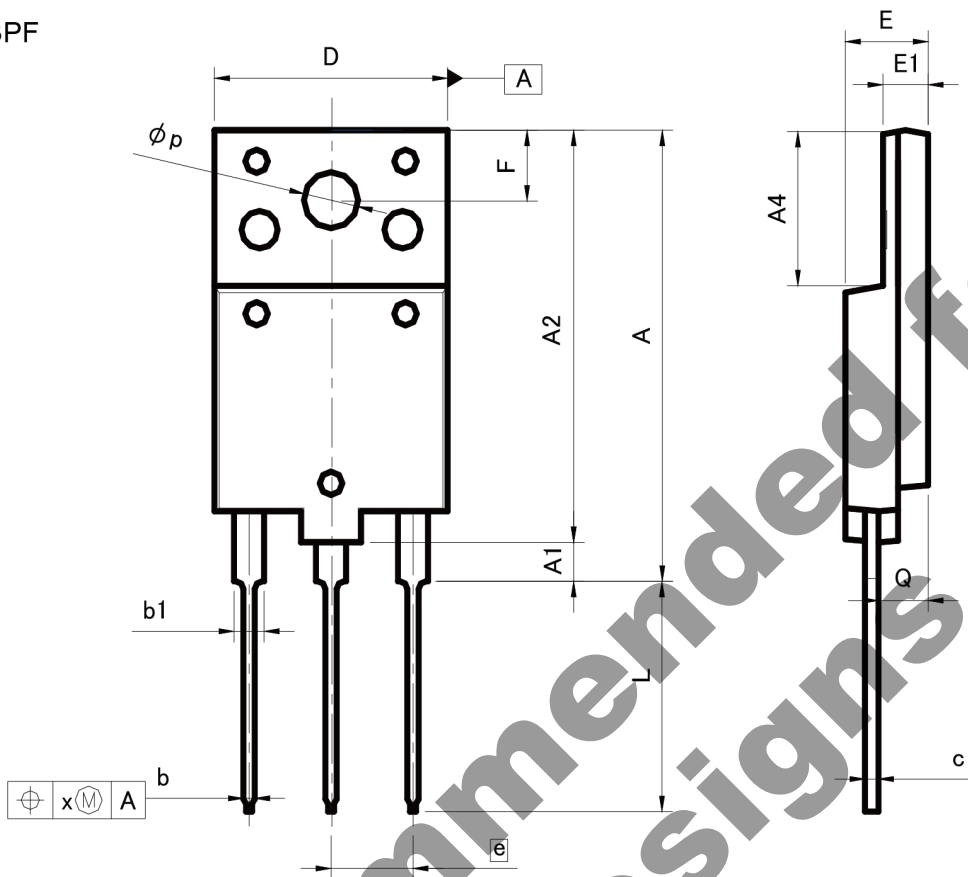


Fig.5-2 di/dt Waveform



●Dimensions

TO-3PF



DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	26.30	26.70	1.035	1.051
A1	2.30	2.70	0.091	0.106
A2	26.30	26.70	1.035	1.051
A4	9.80	10.20	0.386	0.402
b	0.65	0.95	0.026	0.037
b1	1.80	2.20	0.071	0.087
c	0.80	1.10	0.031	0.043
D	15.30	15.70	0.602	0.618
E	5.30	5.70	0.209	0.224
e	5.45		0.215	-
E1	2.80	3.20	0.110	0.126
F	4.30	4.70	0.169	0.185
L	14.60	15.00	0.575	0.591
p	3.40	3.80	0.134	0.150
Q	3.10	3.50	0.122	0.138
x	-	0.50	-	0.020

Dimension in mm/inches

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